HD31125
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Small and light weight bench-top chassis
Class AB linear GaAsFET hybrid design
Instantaneous wide bandwidth
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness



ELECTRICAL SPECIFICATIONS

Parameter	Specification	Notes
Operating Frequency Range	6.0 - 18.0 GHz	
Power Output	10 Watt Min	Saturated CW
Power Gain	40 dB Min	
Power Gain Flatness	4.0 dB p-p Max	
Input Return Loss	10 dB Min	Relative to 50 Ohm
2-Tone Intermodulation (IMD)	-30 dBc Typ	33dBm/Tone, Δ = 1MHz
Harmonics	-20 dBc Typ	At rated Pout
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	100 - 240 VAC	
Power Consumption	150 Watt Max	At rated Pout
Max Input Power Protection	+5 dBm	<10 Seconds without damage
Load VSWR Protection	∞ : 1	<1 Minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Ambient Temperature	0 to +50 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensation

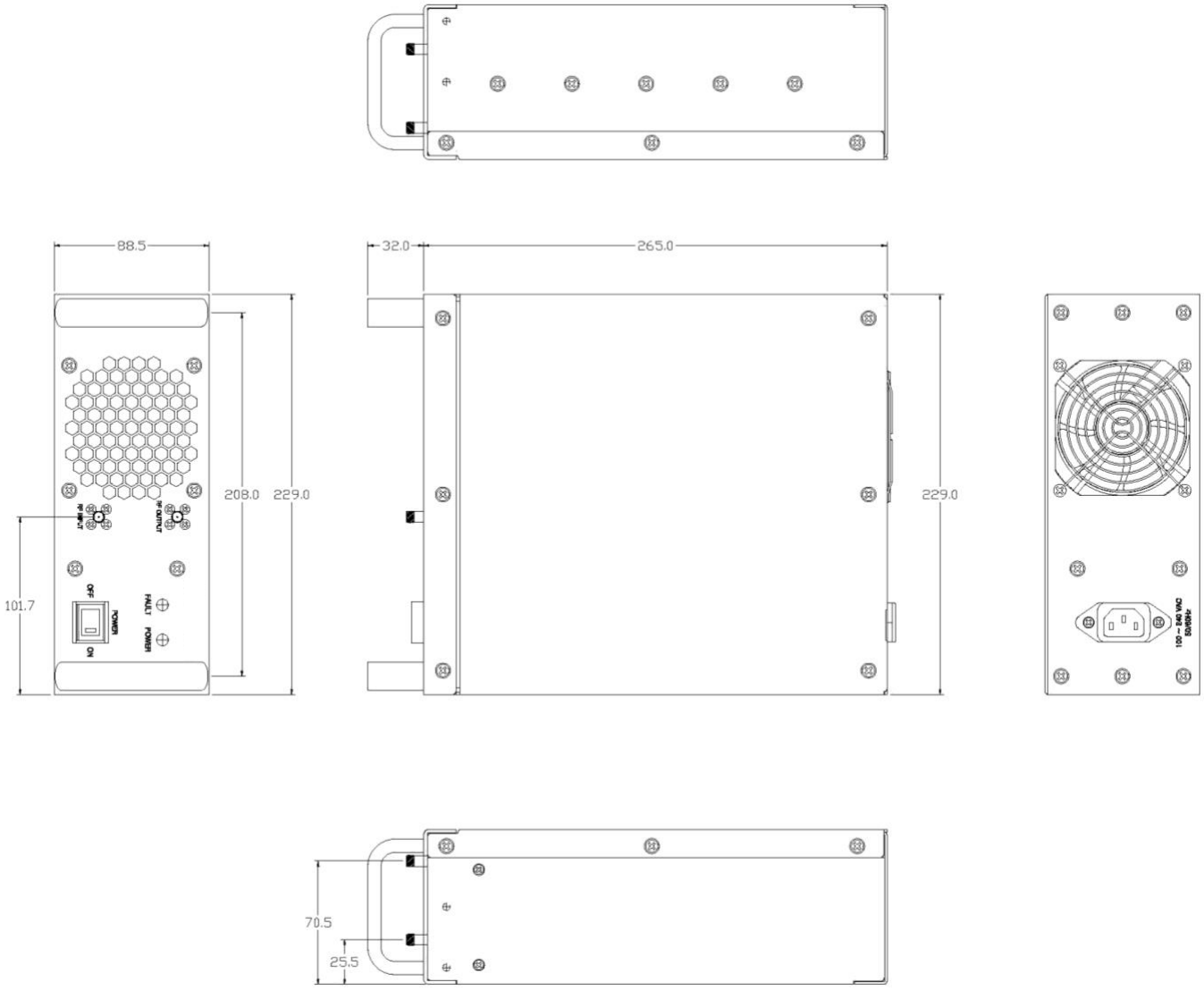
MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions W x H x D	265 x 88 x 229 mm	Bench Top
Weight	8 kg.	
RF Connectors In/Out	Type-N Female	Front Panel Standard
AC Power / Interface Connector	IEC 60320-C14 / 9-Pin D-Sub	
Cooling	Built in Fan Cooling	
OPTIONAL: Digital Monitor & Control FWD, REV, VSWR, GAIN, ALC, V & I, TEMP	Ethernet RJ-45 TCP/IP, RS422/485 Optional GPIB Interface	LCD available in a 2U Chassis

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OUTLINE DRAWING



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